Abstracts

Class-A GaAs FET Power Amplifier Design for Optimizing Intermodulation Product

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Since optimizations of amplifier gain and cutoff frequency f of FET are important to minimize nonlinear distortion, intermodulation products of Class-A GaAs FET amplifier is extensively estimated. output back-off and power added efficiency at any specified D/U ratio are determined under various matching condition using FET's with different f/sub T/. For optimum design of the amplifier, new charts are given which show the back-off and efficiency at the specified D/U ratio as functions of small-signal gain and ratio of operating frequency to f/sub T/.

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